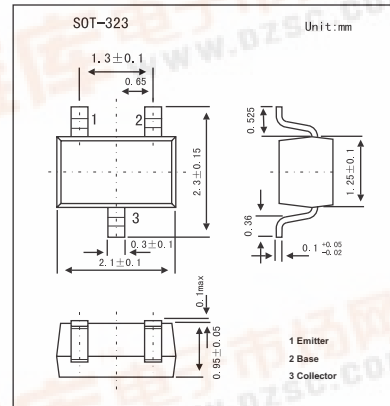


SMD Type Transistors

Silicon PNP Epitaxial  
2SA1586

Features

- High voltage and high current.
- Excellent hFE linearity.
- High hFE.
- Low noise.
- Small package.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>c</sub>	-150	mA
Base current	I <sub>b</sub>	-30	mA
Collector power dissipation	P <sub>c</sub>	100	mW
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature range	T <sub>stg</sub>	-55 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector cut-off current	I <sub>cBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-2mA	70		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA		-0.1	-0.3	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-1mA	80			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		4	7	pF
Noise figure	NF	V <sub>CE</sub> =-6V, I <sub>C</sub> =-0.1mA, f=1kHz, R <sub>g</sub> =10kΩ		1.0	10	dB

hFE Classification

Marking	SO	SY	SG
hFE	70~140	120~240	200~400

